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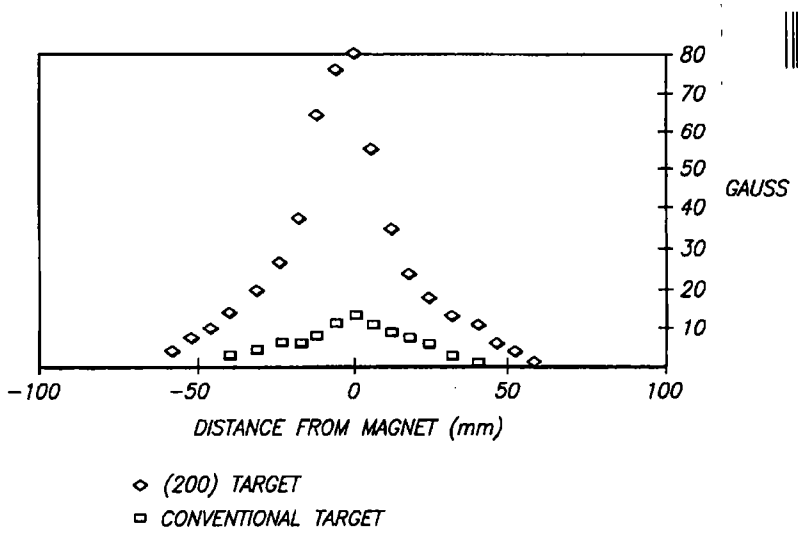
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(54) Title: PHYSICAL VAPOR DEPOSITION COMPONENTS AND METHODS OF FORMATION



ACTION

(57) Abstract: A PVD component forming method includes inducing a sufficient amount of stress in the component to increase magnetic pass through flux exhibited by the component compared to pass through flux exhibited prior to inducing the stress. The method may further include orienting a majority crystallographic structure of the component at (200) prior to inducing the stress, wherein the induced stress alone is not sufficient to substantially alter surface grain appearance. Orienting structure may include first cold working a component blank to at least about an 80% reducton in cross-sectional area. The cold worked component blank can be heat treated at least at about a minimum recrystallization temperature of the component blank. Inducing stress may include second cold work to a reduction in cross-sectional area between about 5% to about 15% of the heat treated component. At least one of the first and second cold working can be unidirectional.

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